

TN1205H

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High temperature 12 A SCRs

Features

- Medium current SCRs
- High static and dynamic commutation
- RoHS (2002/95/EC) compliant
- 600 V V_{DRM}, V_{RRM}
- 150 °C max. T_i turn-off capability

Application

- General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- Inrush current limiting circuits
- Over-voltage crowbar protection

Description

Available in standard gate triggering levels, the TN1205H SCR series has very high switching capability up to junction temperature of 150 °C.

These products fit all modes of control found in applications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition and voltage regulation circuits mainly in areas on which the ambient temperature is hot with difficult ventilation or increase of power density is required.

Through-hole or surface-mount packages provide performance in a limited space area.

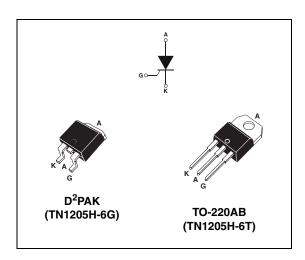


Table 1. Device summary

Order code	Package	V _{DRM} , V _{RRM}	I _{GT}	
TN1205H-6T	TO-220AB	600 V	2 to 5 mA	
TN1205H-6G	D ² PAK	000 V	21051114	

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Table 2. Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit			
I _{T(RMS)}	On-state rms current (180° conduction angle)		12	Α		
I _{T(AV)}	Average on-state current (180° conduction angle)	D^2 PAK $T_c = 136 ^{\circ}C$		7.6	Α	
	Non repetitive aurea peak on state aureat	$t_{p} = 8.3 \text{ ms}$	T 05 °C	126	^	
I _{TSM}	Non repetitive surge peak on-state current	t _p = 10 ms	T _j = 25 °C	120	Α	
l ² t	I^2t Value for fusing $t_p = 10 \text{ ms}$				A ² S	
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state voltage	V _{DRM} , V _{RRM} +100	٧			
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $I_{T} \le 100 \text{ ns}$		T _j = 150 °C	100	A/µs	
I _{GM}	Peak gate current	Peak gate current $t_p = 20 \mu s$ $T_j = 150 ^{\circ}C$		4	Α	
P _{G(AV)}	Average gate power dissipation	1	W			
V _{RGM}	Maximum peak reverse gate voltage	5	V			
T _{stg} T _j	Storage junction temperature range Operating junction temperature range	- 40 to + 150	°C			
T _L	Maximum lead temperature for soldering during 10	260	°C			

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions	Value	Unit			
la-	I_{GT} $V_D = 12 \text{ V}, R_L = 33 \Omega$		MIN.	2	mA	
'GT			MAX.	5	IIIA	
V _{GT}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$		MAX.	1.3	V	
V_{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$		MIN.	0.2	V	
I _H	$I_T = 500 \text{ mA gate open}$ MAX.				mA	
ΙL	I _G = 1.2 I _{GT}	MAX.	40	mA		
dV/dt	V = 67% V gate open	T _j = 125 °C	MIN.	200	V/µs	
u v/ut	$V_D = 67\% V_{DRM}$ gate open $T_j = 150 \text{ °C}$		IVIIIN.	100	ν/μ5	
t _{gt}	$I_{TM} = 40 \text{ A}, V_D = 500 \text{ V}, I_G = 100 \text{ mA}, dI_G/dt = 5 \text{ A/}\mu\text{s}$ typ.		typ.	1.9	μs	
tq	$ \begin{array}{c} V_{DM} = 335 \text{ V, Tj} = 125 \text{ °C, } I_{TM} = 20 \text{ A, } V_{R} = 25 \text{ V, } (dI_{T}/dt)_{Max} = 30 \text{ A/}\mu\text{s,} \\ dV_{D}/dt = 50 \text{ V/}\mu\text{s, } R_{GK} = 100 \Omega \end{array} $		65	μs		

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Table 4. Static characteristics

Symbol	Test conditions	Value	Unit		
V _T	$I_{TM} = 24 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C		1.6	V
V_{TD}	Threshold voltage	T _j = 150 °C		0.8	V
R _d	Dynamic resistance	T _j = 150 °C	MAX.	30	mΩ
		T _j = 25 °C	IVIAA.	5	μΑ
I _{DRM} I _{RRM}	$V_{DRM} = V_{RRM}$	T _j = 125 °C		1	A
TITIVI		T _j = 150 °C		3	mA

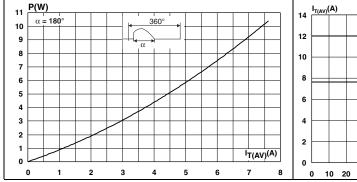
Table 5. Thermal resistance

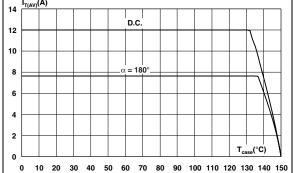
Symbol	Param	Value Max.	Unit		
R _{th(j-c)}	Junction to case (DC)			1.3	°C/W
R _{th(j-a)} Junction to ambient (DC)	lungtion to ambient (DC)	$S^{(1)} = 1 \text{ cm}^2$	D ² PAK	45	°C/W
	Sunction to ambient (DC)		TO-220AB	60	C/VV

^{1.} S = Copper surface under tab

Figure 1. Maximum average power dissipation vs. average on-state current

Figure 2. Average and DC on-state current vs. case temperature





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Figure 3. Average and DC on-state current vs. ambient temperature

Figure 4. Relative variation of thermal impedance vs. pulse duration

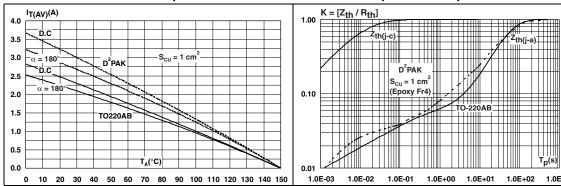


Figure 5. Relative variation of I_{GT} , V_{GT} , I_{H} , I_{L} vs. junction temperature (typical values)

Figure 6. Relative variation of static dV/dt immunity vs. junction temperature (typical values)

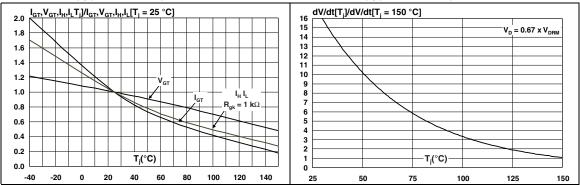
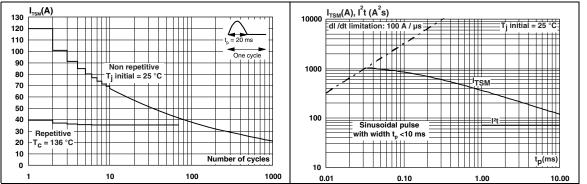


Figure 7. Surge peak on-state current vs. number of cycles

Figure 8. Non repetitive surge peak on-state current and corresponding value of I²t vs. sinusoidal pulse width



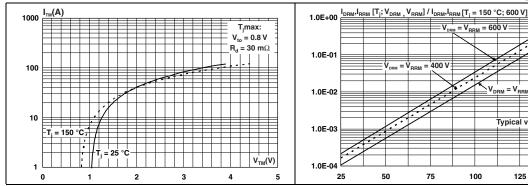
TN1205H **Characteristics**

On-state characteristics Figure 9. (maximum values)

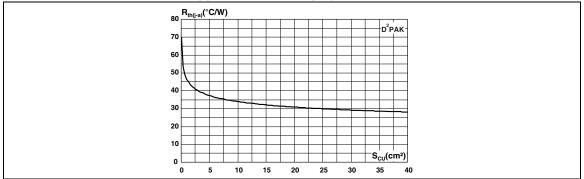
Figure 10. Relative variation of leakage current vs. junction temperature for different values of blocking voltage

Typical value

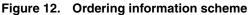
T_i(°C)

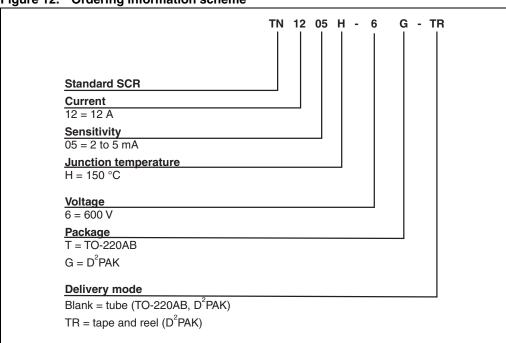


Thermal resistance junction to ambient vs. copper surface under tab (D²PAK, printed Figure 11. circuit board FR4, copper thickness: 35 µm)



2 Ordering information scheme





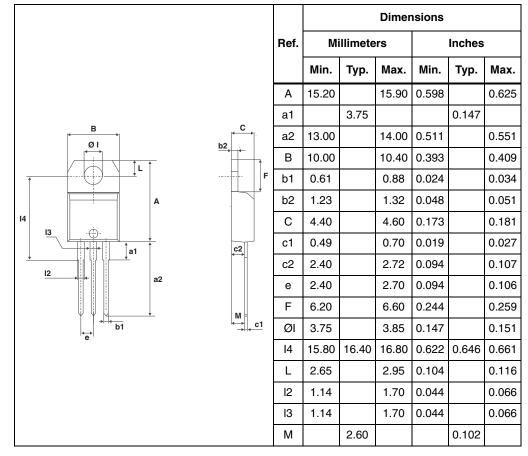
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3 Package information

- Epoxy meets UL94, V0
- Lead-free package

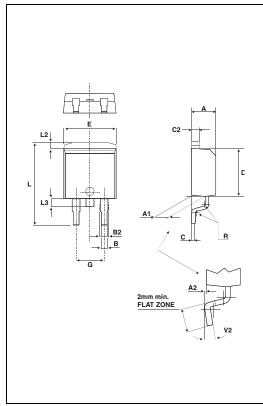
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Table 6. TO-220AB dimensions



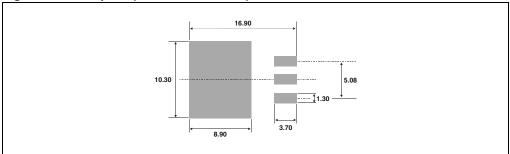
Package information TN1205H

Table 7. D²PAK Dimensions



			Dimer	sions		
Ref.	Mi	illimete	ers		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.048	0.055	
С	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
Е	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R	0.40			0.016		_
V2	0°		8°	0°		8°

Figure 13. Footprint (dimensions in mm)



TN1205H Ordering information

4 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
TN1205H-6T	TN1205H6T	TO-220AB	2.0 g	50	Tube
TN1205H-6G	TN1205H6G	D ² PAK	1.5 g	50	Tube
TN1205H-6G-TR	TN1205H6G	D ² PAK	1.5 g	1000	Tape and reel

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
17-Feb-2011	1	First issue.
26-Sep-2011	2	Corrected typographical error in Features and Description.
17-Jan-2012	3	Updated units for t _{gt} in <i>Table 3</i> .

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